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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Park et al.

Serial No. : 10/618,191

Group Art Unit: 2818

Filed : 07/10/2003

Examiner: HOANG, Q.

For : FLASH MEMORY CELL HAVING REDUCED
LEAKAGE CURRENT

AMENDMENT AND RESPONSE

Commissioner for Patents
P.O Box 1450
Alexandria, VA 22313-1450

Sir:

In response to the Office Action mailed 11/02/2004, please enter and consider the following remarks and arguments for the above captioned patent application.

Amendments to the Claims are reflected in the listing of claims, which begins on page 2 of this paper.

Amendments to the Drawings begin at page 7 of this paper.

Remarks/Arguments begin on page 8 of this paper.

An **Appendix** including a replacement sheet and an annotated sheet is attached at the end of this paper.